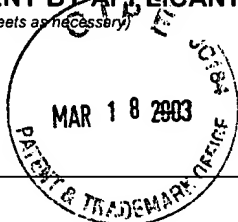


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Application Number	09/945554
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Dickey, Thomas

Sheet 1 of 5

Attorney Docket No: 1303.028US1

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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JD	US-2002/0106536	08/08/2002	Lee, Jongho , et al.	428	702	02/02/2001
JD	US-2002/0137250	09/26/2002	Nguyen, B. , et al.	438	53	03/15/2002
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Application Number	09/945554
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Dickey, Thomas

Sheet 2 of 5

Attorney Docket No: 1303.028US1

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JB	US-6,069,380	05/01/2000	Chou, , et al.	257	315	
JB	US-6,124,729	09/26/2000	Noble, W. P., et al.	326	41	02/27/1998
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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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Sheet 3 of 5

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Application Number	09/945554
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Dickey, Thomas

Attorney Docket No: 1303.028US1

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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4/21/02

Substitute Disclosure Statement Form (PTO-1449)

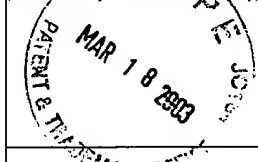
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<b>Application Number</b>	09/945554
<b>Filing Date</b>	August 30, 2001
<b>First Named Inventor</b>	Forbes, Leonard
<b>Group Art Unit</b>	2826
<b>Examiner Name</b>	Dickey, Thomas

Sheet 4 of 5

Attorney Docket No: 1303.028US1

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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